

Free RoHS

2.69V~5.5[V]

1.2 [V](Typ.)

1.5 [V](Typ.)

1.8 [V](Typ.)

3.0 [A] (Max.)

±2.0[%](-40~125°C)

2.25 [MHz] (Typ.)

0[µA](Typ., 25°C) -40~+125°C

Secondary power supply series for automotive 2.69 to 5.5V, Fixed Output, 2.25MHz

# Synchronous Step-Down Converter

# **BD9053xEFJ-C Series**

# General Description

The BD9053xEFJ-C series is a synchronous rectification type step-down DC/DC converter with a 2.25MHz fixed frequency that operates in with an input voltage range of 2.69V-5.5V. It has an integrated feedback resistor that supplies a fixed output voltage of 1.2V/1.5V/1.8V and a phase compensation constant. Applications can be created with a minimum of three external components. Moreover, the integrated Pch and Nch output MOSFET can supply a maximum output current of 3A.

#### Features

- Integrated output feedback resistors and phase compensation network, contributes to minimize external components for the applications.
- Excellent load response through current mode control
- Integrated Pch and Nch output MOSFET
- Integrated overcurrent protection with auto-reset
- Integrated output overvoltage detection/
- short-circuit detection
- Integrated TSD and UVLO
- Light load mode/PWM fixation operation selection pin

1.0µH

ത

 $\frac{1}{2}$ 

SW 8

PGND 7

MODE 5

(BD90535EFJ-C, VIN=5V, IOUT=3A)

FB 6

# Applications

- Automotive equipment
- Car audio and navigation
- ΤV

10ul

FN

Other electronic equipment

1 PVIN

2 VIN

3 EN

4 GND

Figure 1. Typical application circuit

Typical application circuit

1μF

77

# Key Specifications

- Input voltage range
- Output voltage BD90532EFJ-C BD90535EFJ-C
- BD90538EFJ-C Output voltage accuracy
- Operating frequency
- Maximum output current
- Circuit current at standby Operational temperature range
- Package

HTSOP-J8

4.90 mm×6.00 mm×1.00 mm



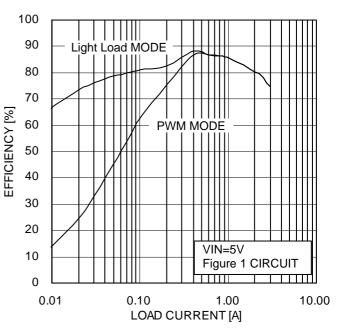


Figure 2. Efficiency (BD90535EFJ-C)

OProduct structure : Silicon monolithic integrated circuit OThis product is not designed to be radiation resistant.

22µF

MODE



# ● Pin Configuration [TOP VIEW]

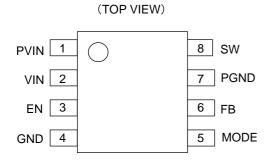


Figure 3. Pin arrangement diagram

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	Pin	Symbol	Function		
	1	PVIN	Power supply pin for output FET		
	2	VIN	Power supply pin		
	3	EN	Enable pin		
	4	GND	GND pin		
	5	MODE	Light load mode/Fixed PWM mode select pin		
	6	FB	Output feedback pin		
	7	PGND	GND pin for output FET		
	8	SW	SW pin		

Pin Description

#### Block diagram

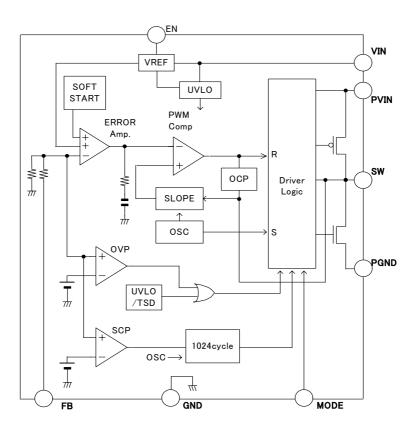


Figure 4. Block diagram

Block operation descriptions

Standby

The circuit enters the state of standby when the EN pin is set to 0.7V or less. All the circuits, such as internal reference voltage VREF, oscillators OSC, and drivers are turned off during standby, and current consumption of the power supply becomes  $0\mu A(25^{\circ}C, Typ.)$ . Via the FB pin, the output capacitor is discharged at a resistance of  $1k\Omega$ .

Start operation

The circuit starts operating when EN pin is set to 2.1V or more. A soft start circuit (SOFT START) is integrated to prevent inrush current to the capacitor when starting. The output voltage reaches a set voltage with 1ms(Typ.) while following the startup of the soft start circuit. There is a delay of about 200µsec until the soft starts begins after the EN pin is turned on and the internal logic operation is started. In order to prevent a defective start, the short-circuit protection is not active during startup.

Error amplifier and phase compensation

The voltage of the output feedback pin(FB) is compared with an internal reference voltage. The voltage corresponding to the difference will be generated, and sent to the PWM comparator which determines the duty ratio of the output. The feedback resistor which determines the output voltage, resistance for compensations, and the capacitor are integrated into the BD9053xEFJ-C series.

Oscillator

The 2.25MHz(Typ.) internally fixed clock is generated and sent to the slope generation circuit (SLOPE) and to the driver.

■ Light load mode and Forced PWM mode

BD90535EFJ-C operates in the light load mode when the MODE pin is set to 0.7V or less. When the output load current is small, the switching operation automatically becomes intermittent in the light load mode. The efficiency at light load improves compared to the Forced PWM mode because the switching loss is suppressed by operating intermittently. The intermittently operating load current level changes depending on the input voltage, inductor value, etc.

If the MODE pin is set to 2.1V or more, the chip operates in Forced PWM mode. In the Forced PWM mode, the efficiency at a light load decreases compared with the light load mode. However, because of the fixed frequency switching through the entire load range, noise is more easily countered.

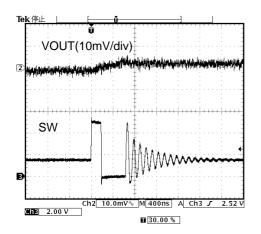


Figure 5. Switching operation at light load mode

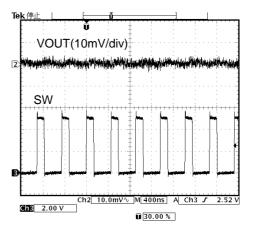


Figure 6. Switching operation at PWM mode

Overcurrent detection

When in the output stage the current flowing to the Pch FET is 3.0A(Min.) or more, the Pch FET is turned off and the power supply to the output is intercepted. The overcurrent detection is operated every cycle, limits the switching duty, and returns at the next clock cycle.

# Output short-circuit detection

The output short-circuit detection circuit (SCP) detects a short-circuit of the output when output voltage falls below 70% of a set value during 1024 cycles of the frequency. In this case, the Pch FET and Nch FET of the output are turned off, and the power supply is intercepted. The count is reset when the output voltage returns to 70% or more before 1024 cycles, and the output voltage returns to the set value.

This SCP automatically resets when after 1024 cycles of the frequency after detecting the short-circuit, and switching is restarted. Resetting triggers the soft start operation because the internal soft start circuit is initialized when the short-circuit detection is activated. The short-circuit detection circuit is not active while soft start is starting. In case the short-circuit continues after resetting, the cycle of starting with a soft start, turning off the output after 1024 cycles, and returning after 1024 cycles is repeated.

#### Output overvoltage detection

When the output overvoltage detection circuit (OVP) detects that the output voltage is exceeding 120% of a set value, the Pch FET and Nch FET of the output are turned off and the power supply is intercepted. Switching is restarted if after the power supply interception the output decreases and the overvoltage situation is released. The overvoltage detection voltage and the release voltage have a hysteresis of about 100mV.

# UVLO

The UVLO circuit is activated and shuts down the circuit when the input voltage (VIN) decreases to 2.6V or less. When the UVLO is activated, the control circuit of the error amplifier, the oscillator, the driver and the output are turned off. Via the FB pin, the output capacitor is discharged at a resistance of  $1k\Omega$ . Afterwards, UVLO is released when the input voltage VIN rises to 2.69V or more, and the output is restored. The output voltage starts with soft start when UVLO is reset.

#### Thermal shutdown(TSD)

Thermal shutdown (TSD) is activated when the IC junction part temperature exceeds 175 °C(Typ.). When the TSD is activated the control circuit of the error amplifier, the oscillator, the driver and the output are turned off. There is hysteresis in the detection temperature of TSD, which is reset when the junction temperature decreases to 150°C(Typ.) or less. The output voltage starts with soft start when TSD is reset.

# •Absolute maximum rating

Parameter	Symbol	Rating	Unit
VIN voltage	VIN	-0.3~7 *1	V
PVIN voltage	PVIN	-0.3~7 *1	V
EN voltage	EN	-0.3~7	V
SW voltage	SW	-1.0~PVIN *1	V
FB voltage	FB	-0.3~7	V
MODE voltage	MODE	-0.3~7	V
Power dissipation	Pd	3.75 *2	W
Operating temperature range	Topr	-40~+125	°C
Storage temperature range	Tstg	-55~+150	°C
Junction temperature	Tj	+150	°C

\*1 Pd should not be exceeded.

\*2 33.3mW/°C reduction when Ta $\geq$ 25°C if mounted on 4 layers glass epoxy board of 70mm×70mm×1.6mm

# ●Recommended operating range(Ta=-40~+125°C)

Parameter	Symbol	Rating	Unit
VIN voltage	VVIN	2.69~5.5	V
PVIN voltage	VPVIN	2.69~5.5	V
EN voltage	VEN	0~5.5(*1)	V
MODE voltage	VMODE	0~5.5	V
Output current	ISW	0~3	А

\*1 The circuit goes into test mode when the EN pin is set at 6V or higher.

#### ● Electrical characteristics (unless otherwise specified: Ta=-40~+125°C, VIN=PVIN=5V, EN=3.3V)

Deveneter	Querrahad	Ratings			11-14	Conditions	
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Standby circuit current	IST	-	0	1	μA	EN=0V, Ta=25°C	
Circuit current	ICC	-	650	1300	μA	FB=VFB+0.1V, Ta=25°C	
UVLO detection voltage	VUVLO1	2.30	2.45	2.60	V	Sweep down	
UVLO release voltage	VUVLO2	2.40	2.55	2.69	V	Sweep up	
EN threshold voltage	VEN	0.7	1.4	2.1	V		
EN inflow current	IEN	0.2	0.7	1.2	μA	EN=3.3V	
Operating frequency	FOSC	1.8	2.25	2.7	MHz		
Output voltage(BD90532EFJ-C)	VFB	1.176	1.20	1.224	V	lo=0mA	
Output voltage(BD90535EFJ-C)	VFB	1.470	1.50	1.530	V	lo=0mA	
Output voltage(BD90538EFJ-C)	VFB	1.764	1.80	1.836	V	lo=0mA	
FB pull-down resistance	RFB	0.4	1	2	MΩ	FB=VFB	
Soft start time	TSS	0.4	1	2	ms		
Pch FET ON resistance	PRON	-	85	-	mΩ		
Nch FET ON resistance	NRON	-	70	-	mΩ		
Overcurrent detection current	IOCP	-	6.5	-	A		
Output overvoltage detection voltage	VOVP	Тур. -0.15	VFB × 1.2	Тур. +0.15	V		
Output short-circuit detection voltage	VSCP	Тур. -0.15	VFB × 0.7	Тур. +0.20	V		
MODE threshold voltage	VMODE	0.9	1.6	2.3	V		
MODE inflow current	IMODE	3.5	7	14	μA	MODE=3.3V	

# Typical Performance Curve

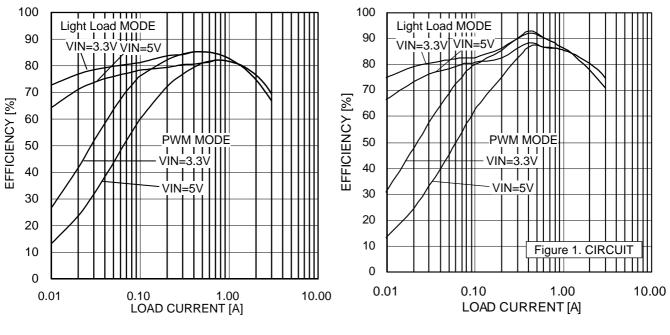




Figure 8. Efficiency(BD90535EFJ-C)

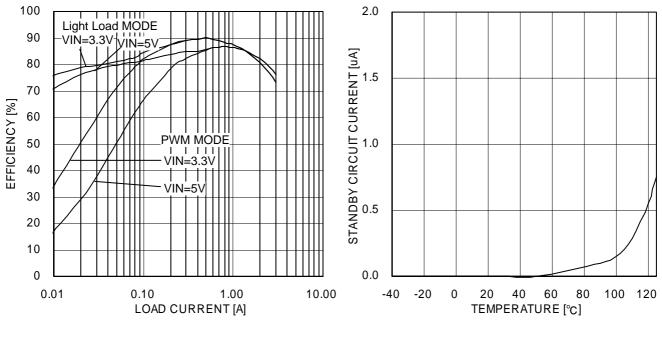
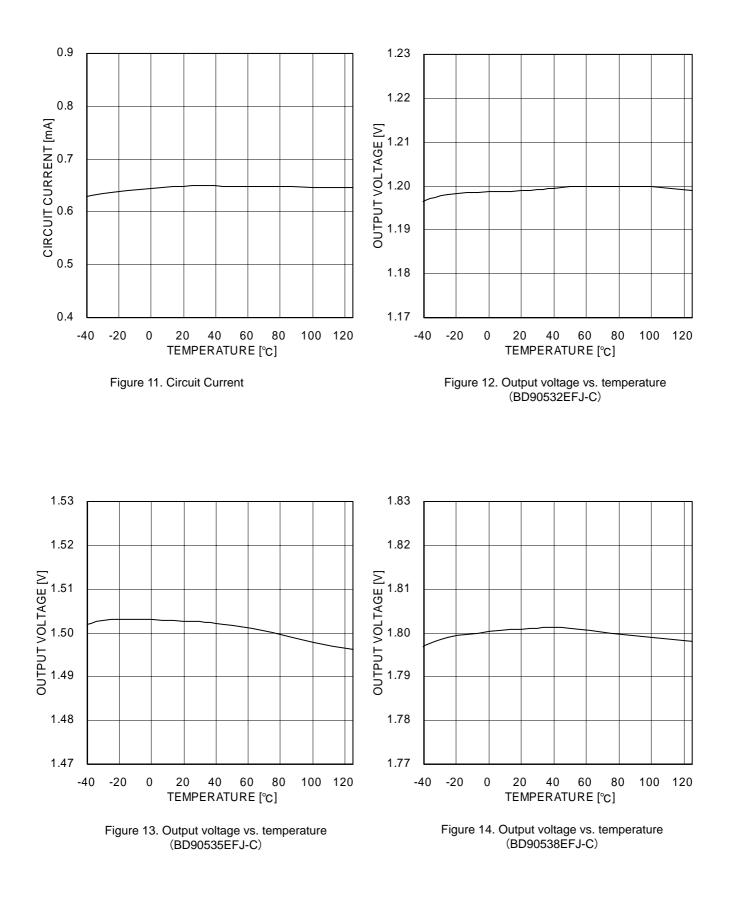
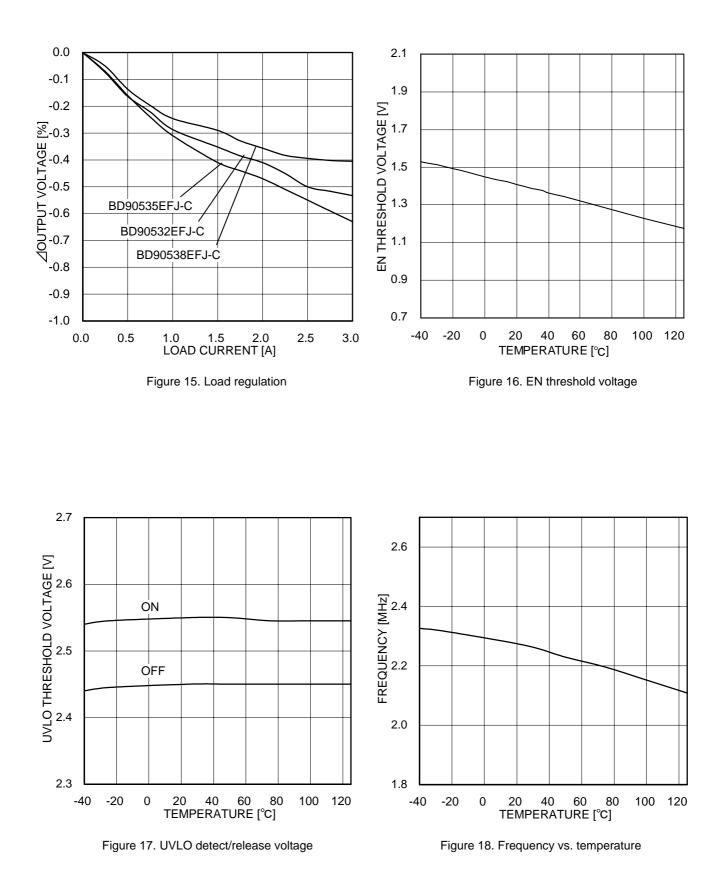
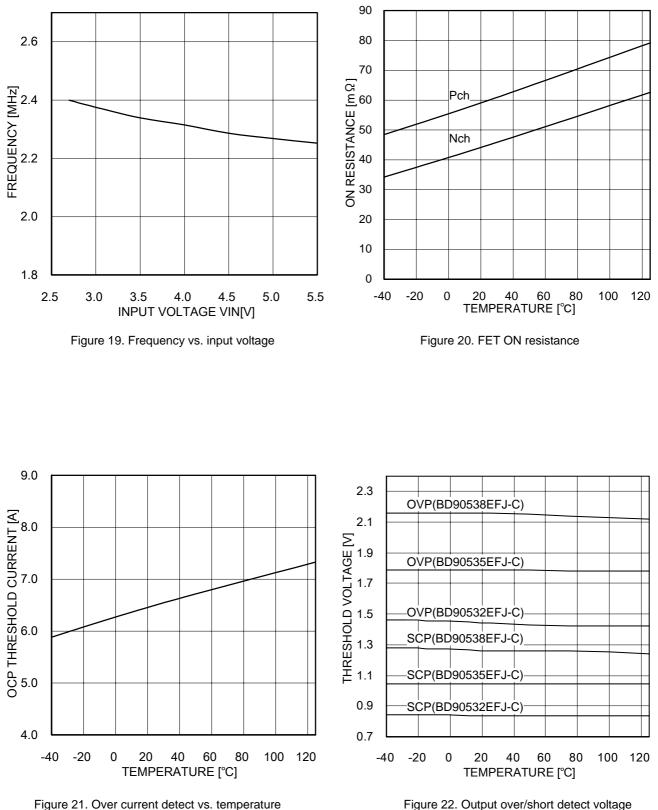


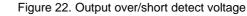
Figure 9. Efficiency(BD90538EFJ-C)

Figure 10. Standby circuit current

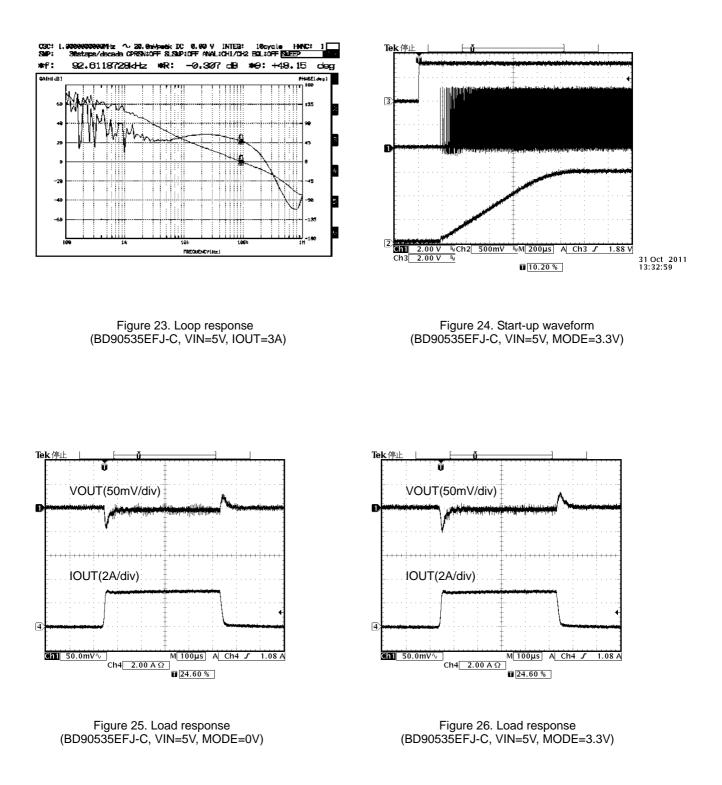








The characteristics below are reference data which are measured with the typical application circuit as shown in Figure 1 Also, these characteristics are influenced by the external components and board layout.



# Timing chart Start-up VIN, PVIN ΕN Setting voltage VOUT 1ms (Typ.) Figure 27. Start-up OCP -----OCP level IOUT Setting voltage VOUT×0.7 VOUT 1024cycle 1024cycle 1ms (Typ.) Figure 28. OCP SCP VOUT short to GND VOUT V sw 1024cycle 1024cycle 1024cycle 1ms(Typ.)

Figure 29. SCP

•Selection of external components

Selection of inductor The inductor value significantly influences the output ripple current. The larger

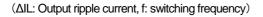
the coil is, the more the ripple current drops will be as shown in the equation below.

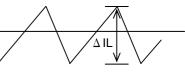
$$\Delta IL = \frac{(PVIN-VOUT) \times VOUT}{L \times PVIN \times f} \quad [A]$$

An inductor with a low value will cause the ripple current to increase and also causes an increase of the ripple element of the output voltage. The optimal output ripple current setting is between 10% ~ 30% of the maximum output current.

 $\Delta IL = 0.2 \times IOUTmax. [A]$ 

$$L = \frac{(PVIN-VOUT) \times VOUT}{\Delta IL \times PVIN \times f}$$
[H]





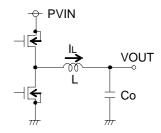


Figure 30. Ripple current

Supplying the coil with a current exceeding the coil's rated current will cause magnetic saturation of the coil and will decrease the efficiency of the coil. Please allow for a sufficient margin in selecting the inductor to ensure that the peak current does not exceed the inductor's rated current. Please select a coil with a small resistance element (DCR, ACR) to reduce the coil loss, and to improve efficiency.

Selection of input capacitor

The input capacitor serves to lower the impedance of the power supply connected to the input pin (VIN, PVIN). An increase of the impedance of this power supply can cause input voltage instability and may negatively impact oscillation and ripple rejection characteristics. Therefore, it is necessary to place an input capacitor in close proximity to the VIN, PVIN, GND and PGND pins.

We recommend selecting a ceramic capacitor with a value of 10uF or more that influenced by changes in temperature as little as possible and that has a sufficiently large permissible ripple current. The ripple current RMS can be calculated using the following equation.

$$IRMS = IOUT \times \sqrt{\frac{VOUT (VIN - VOUT)}{VIN}} [A]$$

Note that depending on the capacitor, the capacitance may be significantly influenced by the applied voltage. Please select a capacitor with good DC bias characteristics and with a high voltage.

#### Selection of output capacitor

We recommend selecting a ceramic capacitor. The ripple element of the output voltage is determined by the ESR of the output capacitor. Please take the permissible voltage of the actual application into consideration when selecting the output capacitor. The ripple element of the output voltage can be calculated by using the equation below. Selecting a low-ESR capacitor can reduce the ripple element of the output voltage. Note that depending on the capacitor, the capacitance may be significantly influenced by the applied voltage. Please select a acapacitor with good DC bias characteristics and with a high voltage.

$$\Delta V_{PP} = \Delta I_L \times R_{ESR} + \frac{\Delta I_L}{Co} \times \frac{Vo}{VIN} \times \frac{1}{f} \quad [V] \qquad f: Switching frequency$$

The startup time needs to be within the soft start time. Therefore, please take the following equation into consideration when selecting the output capacitor

$$Co \leq \frac{TSS \times (ILimit - IOUT)}{VOUT}$$
Tss: Soft start time (typ. 1ms)  
ILimit: Overcurrent detection value (min. 3A)

Non-optimal capacitance values may cause startup problems. Especially in cases of extremely large capacitance values, the possibility exists that the inrush current at startup will activate the overcurrent protection, thus not starting the output. Therefore, verification and confirmation with the actual application is recommended.

Selection of Schottky diode

Depending on the application the efficiency may be improved by placing a Schottky diode between the SW pin and PGND pin thereby creating a current path when the synchronous switching (Nch FET) is off. When selecting the Schottky diode ensure that the maximum reverse voltage is higher than the input voltage and that the rated current is higher than the maximum inductor current (the sum of the maximum output current and inductor ripple current).

### Notes on the substrate layout

The substrate layout greatly influences the stable operation of the IC. Depending on the substrate layout the IC might not show its original characteristics or might not function properly. Please note the following points when drawing the substrate layout.

- > The input capacitors C1 and C2 should be placed as close as possible to the VIN, PVIN, GND and PGND pins.
- > The output voltage feedback line should be separated from lines with a lot of noise such as the SW line.
- The GND signal should be separated from the input capacitor and the GND and PGND of the output capacitor and brought together at one point.
- > The output capacitors C3 and C4 should be placed in close proximity to inductor L1.
- The inductor L1 should be placed as close as possible to the SW pin. The pattern area of the SW node should be as small as possible.
- The MODE pin should be pulled down via R3 by GND and pulled up via R2 by VIN. It is also possible to directly supple the MODE pin with voltage.
- The feedback frequency characteristics (phase margin) can be measured by inserting a resistor at the location of R1 and using FRA. However, this should be shorted during normal operation.

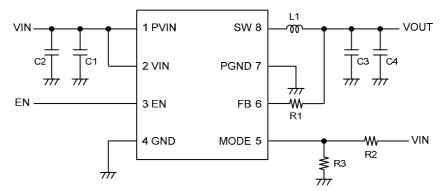
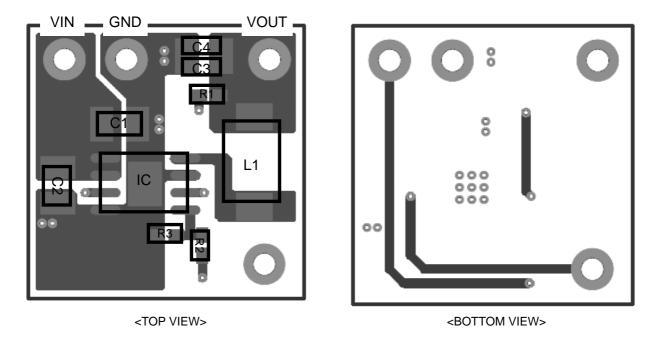
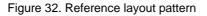


Figure 31. Reference circuit





### Heat dissipation

The maximum allowable junction temperature Tj of BD9053xEFJ-C series is 150°C. In case Tj exceeds 150°C, the temperature protection circuit is activated and the circuit shuts down. Therefore, it is necessary to design the system requirements and the board layout so that the junction temperature does not exceed 150°C in the power-supply voltage, the output load and the operating temperature range.

The maximum junction temperature can be calculated using the ambient temperature Ta, the thermal resistance  $\theta$  a of the package and heat dissipation P of the IC.

Tj = Ta +  $\theta$ ja × P [°C]

The thermal resistance  $\theta_{ja}$  of the package changes depending on the number of layers and the copper foil area of the board.

The heat dissipation PTOTAL of the IC can be calculated by the equation below.

 $\begin{array}{l} P_{TOTAL} = P_{ICC} + P_{RON} + P_{SW} \left[W\right] \\ P_{ICC} = VIN \times ICC \cdots & \text{Heat dissipation in control circuit} \\ P_{RON} = R_{on} \times lo^2 \cdots & \text{Heat dissipation in output FET} \\ P_{SW} = Tr \times lo \times VIN \times F \cdots & \text{Heat dissipation in switching} \end{array}$ 

ICC: circuit current

Ron: ON resistance of the output FET

F: frequency

All values are specified in the electrical characteristics. Tr is the rise time and fall time at switching. In the standard case is 5nsec and in the max case is 10nsec.

Also, these characteristics are influenced by the external components and board layout.

•Thermal derating characteristic

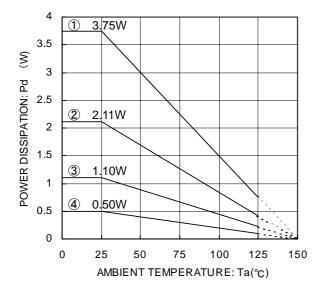
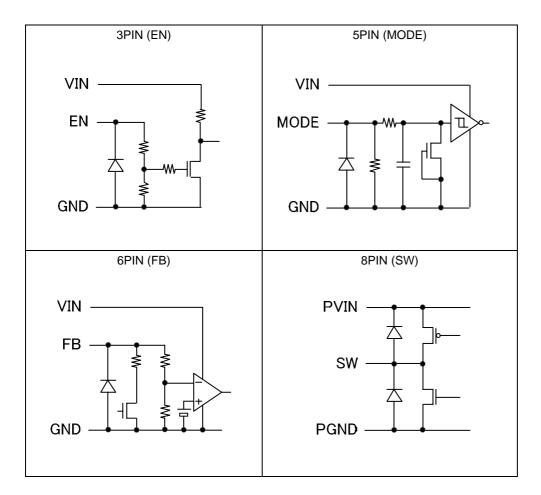


Figure 33. Thermal derating characteristic

IC mounted on ROHM standard board •Board size:70mm×70mm×1.6mm

- •The board and the back exposure heat radiation board part of package are connected with solder.
- ① IC unit, θja=249.5°C/W
- 2 layers board (Copper foil:15mm×15mm), θja =113.6°C/W
- 3 2 layers board (Copper foil: 70mm×70mm), θja =59.2°C/W
- (4) 4 layers board (Copper foil:70mm×70mm),  $\theta ja = 33.3^{\circ}C/W$

# ●I/O equivalence circuit



### Operational Notes

1. Absolute maximum ratings

Exceeding the absolute maximum rating for supply voltage, operating temperature or other parameters may result in damages to or destruction of the chip. In this event it also becomes impossible to determine the cause of the damage (e.g. short circuit, open circuit, etc.). Therefore, if any special mode is being considered with values expected to exceed the absolute maximum ratings, implementing physical safety measures, such as adding fuses, should be considered.

2. Thermal protection circuit (TSD)

If the junction temperature (Tj) exceeds 175°C(Typ.) the thermal protection circuit (TSD) is activated and the output is put in the OFF status. The releasing temperature has hysteresis of about 25°C(typ.). The thermal protection circuit only functions to block thermal overloads from reaching the IC. Its purpose is not to protect the circuit or to guarantee the operations of the IC. Therefore, the IC should not be continuously operated after this circuit has been activated, nor should the IC be used in applications where the activation of this circuit is a prerequisite.

3. Overcurrent protection circuit

This IC incorporates an integrated overcurrent protection circuit that operates in accordance with the rated output capacity. This circuit serves to protect the IC from damage when the load becomes shorted. The protection circuit is effective in preventing damage due to sudden and unexpected accidents. However, the IC should not be used in applications characterized by the continuous or transitive operation of the protection circuit.

4. High temperature, no load behavior

In a situation where there is a high temperature and no load, it might be that the leak current of the output transistor causes output voltage to rise (up to maximum VIN). It case it is expected that in the application conditions the output load drops below 1mA, please place a  $1k\Omega$  resistor at the output in order to prevent an no-load situation.

5. Power dissipation, ASO

Should by any chance the power dissipation rating be exceeded, the rise in temperature of the chip may result in deterioration of the properties of the chip and lead to a decrease of the reliability. Therefore, allow for sufficient margins to ensure use within the power dissipation rating. Also, please ensure in the design that the absolute maximum rating of the output transistor and the ASO are not exceeded when operating the IC.

- 6. Operation in strong electromagnetic fields Use caution when operating in the presence of strong electromagnetic fields, as this may cause the IC to malfunction.
- Connection to the power supply connector A reverse connection to the power supply connector may cause damages to the IC. In order to prevent against reverse connection damages please externally place a diode between the power supply and the power supply pin of the IC.
- Inter-pin shorts and mounting errors
  Use caution when orienting and positioning the IC for mounting on printed circuit boards. Improper mounting may
  result in damage to the IC. Shorts between output pins or between output pins and the power supply or GND pins
  (caused by poor soldering or foreign objects) may result in damage to the IC.
- Short to power supply, short to ground, inter-pin shorts Please avoid shorts between the output pin and the power supply (VIN, PVIN), shorts between the output pin and ground (GND, PGND) and shorts between the output pins.
- 10. Testing on application boards

When testing the IC on an application board, connecting a capacitor directly to a low-impedance pin may subject the IC to stress. Always discharge capacitors completely after each process or step. The IC's power supply should always be turned off completely before connecting or removing it from a jig or fixture during the evaluation process. To prevent damage from static discharge, ground the IC during assembly and use similar precautions during transport and storage.

11. GND potential

The potential of the GND pin must be the minimum potential in the system in all operating conditions. Ensure that no pins are at a voltage below the GND at any time, regardless of transient characteristics.

12. Wiring of VIN and GND

For the wiring of VIN, PVIN, GND and PGND please create a layout with as wide as possible wires and a minimum distance in between the wires. In case of both small signal lines and high current lines, use single-point grounding to separate the small-signal and high current patterns and to ensure that voltage changes stemming from the wiring resistance and high current do not cause any voltage change in the small-signal. Also place a capacitor at the grounding point for stabilization.

13. Capacitor between PVIN and PGND

The capacitor between PVIN and PGND absorbs the steep changes in voltage and current caused by the PWM drive and thereby suppress fluctuations in the PVIN voltage. However, this effect is diminished due to wiring impedance the further the capacitor is removed from the IC.

14. Input pins

This monolithic IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. P-N junctions are formed at the intersection of these P layers with the N layers of other elements, creating a parasitic diode or transistor. Relations between each potential may form as shown in the example below, where a resistor and transistor are connected to a pin:

- With the resistor, when GND> Pin A, and with the transistor (NPN), when GND>Pin B:
- The P-N junction operates as a parasitic diode.
- With the transistor (NPN), when GND> Pin B:
- The P-N junction operates as a parasitic transistor by interacting with the N layers of elements in proximity to the parasitic diode described above.

Parasitic diodes inevitably occur in the structure of the IC. Their operation can result in mutual interference between circuits and can cause malfunctions and, in turn, physical damage to or destruction of the chip. Therefore do not employ any method in which parasitic diodes can operate such as applying a voltage to an input pin that is lower than the (P substrate) GND.

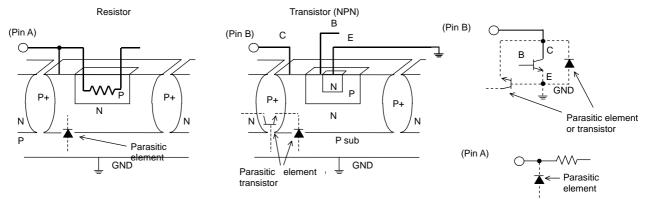


Figure 34. Example of IC structure

15. Application current and constants

The application circuit as shown in Figure 1. and the constants are examples to show the standard operation and application of this IC. In case of creating a design for mass production with different external components please contact ROHM for detailed information.

16. In some applications, the PVIN pin and SW pin potential might be reversed, possibly resulting in circuit internal damage or damage to the elements. For example, while the external capacitor is charged, the PVIN shorts to the GND. To prevent this we recommend reverse polarity diodes in series or placing a bypass diode between the SW pin and PVIN pin.

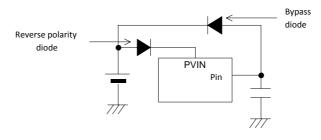
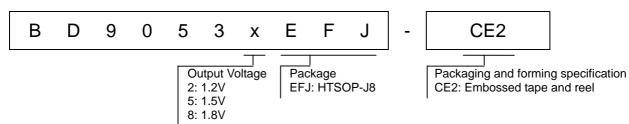


Figure 35. Measure for reverse

#### Note concerning this document

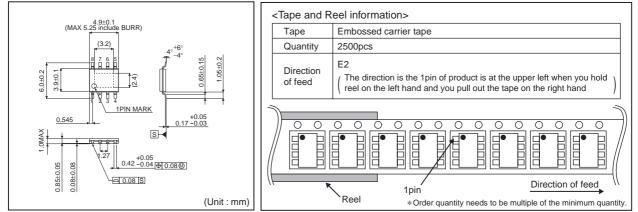
The Japanese version of this document is the official specification. This translation should be seen as a reference to aid reading the official specification. In case of any discrapencies between the two versions, the official version always takes precedence.

# Ordering Information

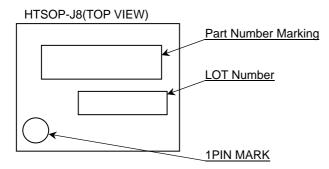


# Physical Dimension Tape and Reel Information

# HTSOP-J8



# Marking Diagram



Product Name Marking
D90532
D90535
D90538

# Revision History

Rev.	Date	Notes
001	2012/05/16	New release
002	2012/09/20	<ul> <li>Add the contents of the model Line-up (BD90532EFJ-C, BD90538EFJ-C) General Description, Key Specifications, Electrical characteristics, Typical Performance Curve, Ordering Information, Marking Diagram, etc.</li> <li>Add the contents that ceramic capacitors are recommended in the description of input and output capacitors in selection of external components</li> <li>Add the maximum value of Tr in the description of heat dissipation</li> </ul>

# Notice

#### **General Precaution**

- 1. Before you use our Products, you are requested to carefully read this document and fully understand its contents. ROHM shall not be in any way responsible or liable for failure, malfunction or accident arising from the use of any ROHM's Products against warning, caution or note contained in this document.
- 2. All information contained in this document is current as of the issuing date and subject to change without any prior notice. Before purchasing or using ROHM's Products, please confirm the latest information with a ROHM sales representative.

#### Precaution on using ROHM Products

- 1. If you intend to use our Products in devices requiring extremely high reliability (such as medical equipment, aircraft/spacecraft, nuclear power controllers, etc.) and whose malfunction or failure may cause loss of human life, bodily injury or serious damage to property ("Specific Applications"), please consult with the ROHM sales representative in advance. Unless otherwise agreed in writing by ROHM in advance, ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of any ROHM's Products for Specific Applications.
- 2. ROHM designs and manufactures its Products subject to strict quality control system. However, semiconductor products can fail or malfunction at a certain rate. Please be sure to implement, at your own responsibilities, adequate safety measures including but not limited to fail-safe design against the physical injury, damage to any property, which a failure or malfunction of our Products may cause. The following are examples of safety measures:
  - [a] Installation of protection circuits or other protective devices to improve system safety
  - [b] Installation of redundant circuits to reduce the impact of single or multiple circuit failure
- 3. Our Products are not designed under any special or extraordinary environments or conditions, as exemplified below. Accordingly, ROHM shall not be in any way responsible or liable for any damages, expenses or losses arising from the use of any ROHM's Products under any special or extraordinary environments or conditions. If you intend to use our Products under any special or extraordinary environments or conditions (as exemplified below), your independent verification and confirmation of product performance, reliability, etc, prior to use, must be necessary:
  - [a] Use of our Products in any types of liquid, including water, oils, chemicals, and organic solvents
  - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
  - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl<sub>2</sub>, H<sub>2</sub>S, NH<sub>3</sub>, SO<sub>2</sub>, and NO<sub>2</sub>
  - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
  - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
  - [f] Sealing or coating our Products with resin or other coating materials
  - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
  - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation (Pd) depending on Ambient temperature (Ta). When used in sealed area, confirm the actual ambient temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

# Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used; if flow soldering method is preferred, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

#### Precautions Regarding Application Examples and External Circuits

- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
- 2. You agree that application notes, reference designs, and associated data and information contained in this document are presented only as guidance for Products use. Therefore, in case you use such information, you are solely responsible for it and you must exercise your own independent verification and judgment in the use of such information contained in this document. ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of such information.

#### **Precaution for Electrostatic**

This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

#### Precaution for Storage / Transportation

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
  - [a] the Products are exposed to sea winds or corrosive gases, including Cl2, H2S, NH3, SO2, and NO2
    - [b] the temperature or humidity exceeds those recommended by ROHM
    - [c] the Products are exposed to direct sunshine or condensation
    - [d] the Products are exposed to high Electrostatic
- Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

#### **Precaution for Product Label**

QR code printed on ROHM Products label is for ROHM's internal use only.

#### **Precaution for Disposition**

When disposing Products please dispose them properly using an authorized industry waste company.

#### Precaution for Foreign Exchange and Foreign Trade act

Since our Products might fall under controlled goods prescribed by the applicable foreign exchange and foreign trade act, please consult with ROHM representative in case of export.

#### **Precaution Regarding Intellectual Property Rights**

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